

Yang Shao

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Systematic Defect Manipulation in Metal Oxide Semiconductors towards High-Performance Thin-Film Transistors. , 2020, , .		0
2	Fully Self-Aligned Homojunction Bottom-Gate Amorphous InGaZnO TFTs with Al Reacted Source/Drain Regions. , 2020, , .		0
3	Homo-Junction Bottom-Gate Amorphous InGaZnO TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	2.1	9
4	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. ACS Applied Materials & Interfaces, 2018, 10, 25850-25857.	8.0	36
5	Ti Film Thickness Influences on the Back Channel Etched Amorphous InGaZnO Thin Film Transistors. , 2018, , .		0
6	24.5: Back-Channel-Etched a-IGZO TFTs with TiO ₂ :Nb Protective Layer. Digest of Technical Papers SID International Symposium, 2018, 49, 263-266.	0.3	0
7	Dynamic Threshold Voltage Modulation in Double-Gate Indium-Gallium-Zinc Oxide Thin-Film Transistors: Influence of the Active Layer Thickness. , 2018, , .		1
8	6.1: Asymmetric Effects of Gate-Bias Stress Voltage on the Stability under Positive and Negative Gate-Bias Stress of a-IGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 597-600.	0.3	2
9	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	2.1	9
10	9: Parylene / Al ₂ O ₃ Double Layer Passivated Amorphous InGaZnO Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1258-1261.	0.3	7
11	Oxygen Interstitial Creation in a-IGZO Thin-Film Transistors Under Positive Gate-Bias Stress. IEEE Electron Device Letters, 2017, 38, 1252-1255.	3.9	41
12	Impact of sputtering power of source/drain metal on performances of a-IGZO thin film transistors fabricated using wet back-channel-etch process. , 2017, , .		1
13	ZnSnO thin-film transistors by reactive co-sputtering of Zn and Sn metal targets. , 2017, , .		1
14	Electron-transport layer free perovskite solar cells with anodized ITO electrode. , 2017, , .		0
15	Indium-Tin-Oxide Thin-Film Transistors With In Situ Anodized Ta ₂ O ₅ Passivation Layer. IEEE Electron Device Letters, 2016, 37, 603-606.	3.9	12
16	A Back-Channel-Etched Amorphous InGaZnO Thin-Film Transistor Technology With Al-Doped ZnO as Source/Drain and Pixel Electrodes. IEEE Transactions on Electron Devices, 2016, 63, 2205-2209.	3.0	15
17	Amorphous Indium Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Technique. IEEE Transactions on Electron Devices, 2016, 63, 1072-1077.	3.0	18
18	Back Channel Anodization Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors Process. IEEE Electron Device Letters, 2015, 36, 357-359.	3.9	9

#	ARTICLE	IF	CITATIONS
19	Low-Voltage a-InGaZnO Thin-Film Transistors With Anodized Thin HfO ₂ Gate Dielectric. IEEE Electron Device Letters, 2015, 36, 573-575.	3.9	51
20	Fabrication of p-type copper oxide thin-film transistors at different oxygen partial pressure. , 2014, , .		6
21	Characteristics of double-gate a-IGZO TFT. , 2014, , .		2
22	A Multi- V_{th} a-IGZO TFT Technology Using Anodization to Selectively Reduce Oxygen Vacancy Concentration in Channel Regions. IEEE Electron Device Letters, 2014, 35, 1248-1250.	3.9	3
23	Anodized ITO Thin-Film Transistors. Advanced Functional Materials, 2014, 24, 4170-4175.	14.9	41
24	Homojunction In ₂ O ₃ -TFTs prepared by anodization technique. , 2014, , .		0
25	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
26	Impacts of substrate heating schemes on characteristics of amorphous indium-gallium-zinc-oxide (a-IGZO) TFTs fabricated on flexible substrates. , 2014, , .		1